Yvon Cordier

List of Publications by Year
in descending order

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224	3,625	159585	223800
papers	citations	30	46
		h-index	g-index

226	226	226	2833
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Gallium Nitride as an Electromechanical Material. Journal of Microelectromechanical Systems, 2014, 23, 1252-1271.	2.5	173
2	Molecular Beam Epitaxy of Group-III Nitrides on Silicon Substrates: Growth, Properties and Device Applications. Physica Status Solidi A, 2001, 188, 501-510.	1.7	142
3	Amplified piezoelectric transduction of nanoscale motion in gallium nitride electromechanical resonators. Applied Physics Letters, 2009, 94, .	3.3	110
4	Growth of thick, continuous GaN layers on 4-in. Si substrates by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2011, 314, 85-91.	1.5	100
5	InAlAs/InGaAs metamorphic HEMT with high current density and high breakdown voltage. IEEE Electron Device Letters, 1998, 19, 345-347.	3.9	85
6	Electromechanical Transconductance Properties of a GaN MEMS Resonator With Fully Integrated HEMT Transducers. Journal of Microelectromechanical Systems, 2012, 21, 370-378.	2.5	82
7	GaN transistor characteristics at elevated temperatures. Journal of Applied Physics, 2009, 106, .	2.5	67
8	AlGaNâˆ•GaN HEMTs on Si(111) with 6.6â€…Wâˆ•mm output power density. Electronics Letters, 2003, 39, 626.	1.0	59
9	Analysis of the AlGaN/GaN vertical bulk current on Si, sapphire, and free-standing GaN substrates. Journal of Applied Physics, 2013, 113, .	2.5	57
10	Tuning the electromagnetic local density of states in graphene-covered systems via strong coupling with graphene plasmons. Physical Review B, 2013, 87, .	3.2	56
11	Power Performance at 40 GHz of AlGaN/GaN High-Electron Mobility Transistors Grown by Molecular Beam Epitaxy on Si(111) Substrate. IEEE Electron Device Letters, 2015, 36, 303-305.	3.9	55
12	Indium content measurements in metamorphic high electron mobility transistor structures by combination of x-ray reciprocal space mapping and transmission electron microscopy. Journal of Applied Physics, 2003, 93, 4219-4225.	2.5	53
13	The critical role of growth temperature on the structural and electrical properties of AlGaN/GaN high electron mobility transistor heterostructures grown on Si(111). Journal of Applied Physics, 2009, 105, 033701.	2.5	50
14	Power Performance of AlGaN/GaN High-Electron-Mobility Transistors on (110) Silicon Substrate at 40 GHz. IEEE Electron Device Letters, 2013, 34, 490-492.	3.9	48
15	Micro and nano analysis of 0.2 Î© mm Ti/Al/Ni/Au ohmic contact to AlGaN/GaN. Applied Physics Letters, 2011, 99, 213504.	3.3	47
16	Demonstration of AlGaN/GaN High-Electron-Mobility Transistors Grown by Molecular Beam Epitaxy on Si(110). IEEE Electron Device Letters, 2008, 29, 1187-1189.	3.9	44
17	Metamorphic In/sub 0.4/Al/sub 0.6/As/In/sub 0.4/Ga/sub 0.6/As HEMTs on GaAs substrate. IEEE Electron Device Letters, 1999, 20, 123-125.	3.9	43
18	Growth of thick GaN layers on 4â€in. and 6â€in. silicon (111) by metalâ€organic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1479-1482.	0.8	42

#	Article	IF	Citations
19	AlGaN/GaN high electron mobility transistors grown on 3C-SiC/Si(111). Journal of Crystal Growth, 2008, 310, 4417-4423.	1.5	41
20	Role of magnetic polarons in ferromagnetic GdN. Physical Review B, 2013, 87, .	3.2	40
21	High Microwave and Noise Performance of 0.17-<tex>$muhbox m$</tex>AlGaNâ€“GaN HEMTs on High-Resistivity Silicon Substrates. IEEE Electron Device Letters, 2004, 25, 167-169.	3.9	38
22	Graphene integration with nitride semiconductors for high power and high frequency electronics. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600460.	1.8	38
23	High-Performance Graphene/AlGaN/GaN Schottky Junctions for Hot Electron Transistors. ACS Applied Electronic Materials, 2019, 1, 2342-2354.	4.3	35
24	Thickness and substrate effects on AlN thin film growth at room temperature. EPJ Applied Physics, 2008, 43, 309-313.	0.7	34
25	Metamorphic In0.3Ga0.7As/In0.29Al0.71As layer on GaAs: A new structure for high performance high electron mobility transistor realization. Applied Physics Letters, 1992, 61, 922-924.	3.3	33
26	Effect of surface preparation and interfacial layer on the quality of SiO2/GaN interfaces. Journal of Applied Physics, 2011, 109, .	2.5	33
27	InAlAs/InGaAs Metamorphic High Electron Mobility Transistors on GaAs Substrate: Influence of Indium Content on Material Properties and Device Performance. Japanese Journal of Applied Physics, 1999, 38, 1164-1168.	1.5	32
28	AlGaN/GaN HEMTs regrown by MBE on epi-ready semi-insulating GaN-on-sapphire with inhibited interface contamination. Journal of Crystal Growth, 2007, 309, 1-7.	1.5	32
29	Homoepitaxy of non-polar ZnO/(Zn,Mg)O multi-quantum wells: From a precise growth control to the observation of intersubband transitions. Applied Physics Letters, 2017, 111, .	3.3	32
30	Capture time versus barrier thickness in quantumâ€well structures measured by infrared photoconductive gain. Applied Physics Letters, 1993, 63, 3312-3314.	3.3	30
31	InAlAs buffer layers grown lattice mismatched on GaAs with inverse steps. Journal of Crystal Growth, 1999, 201-202, 263-266.	1.5	30
32	The indium content in metamorphic As/As HEMTs on GaAs substrate: a new structure parameter. Solid-State Electronics, 2000, 44, 1021-1027.	1.4	30
33	MBE growth of ALGaN/GaN HEMTS on resistive Si(111) substrate with RF small signal and power performances. Journal of Crystal Growth, 2003, 251, 811-815.	1.5	29
34	Development and analysis of low resistance ohmic contact to n-AlGaN/GaN HEMT. Diamond and Related Materials, 2007, 16, 262-266.	3.9	29
35	Elaboration of (111) oriented 3Câ€“SiC/Si layers for template application in nitride epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 9-14.	3.5	28
36	High Lateral Breakdown Voltage in Thin Channel AlGaN/GaN High Electron Mobility Transistors on AlN/Sapphire Templates. Micromachines, 2019, 10, 690.	2.9	28

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37	High-electron-mobility AlGaNâˆ•GaN heterostructures grown on Si(001) by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 133505.	3.3	27
38	Growth mode and electric properties of graphene and graphitic phase grown by argonâ€“propane assisted CVD on 3Câ€“SiC/Si and 6Hâ€“SiC. Journal of Crystal Growth, 2012, 349, 27-35.	1.5	27
39	AlGaN Channel High Electron Mobility Transistors with Regrown Ohmic Contacts. Electronics (Switzerland), 2021, 10, 635.	3.1	27
40	Interplay between relaxation, surface morphology and composition modulation in InAlAs graded buffer layers. Journal of Crystal Growth, 2003, 251, 112-117.	1.5	26
41	Thermal effects in AlGaN/GaN/Si high electron mobility transistors. Solid-State Electronics, 2011, 61, 1-6.	1.4	26
42	Microwave performance of 0.4 Î¼m gate metamorphic In0.29Al0.71As/In0.3Ga0.7As HEMT on GaAs substrate. Electronics Letters, 1993, 29, 169.	1.0	25
43	Growth of GaN based structures on Si(110) by molecular beam epitaxy. Journal of Crystal Growth, 2010, 312, 2683-2688.	1.5	25
44	MBE grown InAlAs/InGaAs lattice mismatched layers for HEMT application on GaAs substrate. Applied Surface Science, 1998, 123-124, 734-737.	6.1	24
45	Enhancement-mode Al/sub 0.66/In/sub 0.34/As/Ga/sub 0.67/In/sub 0.33/As metamorphic HEMT, modeling and measurements. IEEE Transactions on Electron Devices, 2001, 48, 1037-1044.	3.0	24
46	AlGaN/GaN HEMTs on (001) Silicon Substrate With Power Density Performance of 2.9 W/mm at 10 GHz. IEEE Transactions on Electron Devices, 2010, 57, 1497-1503.	3.0	24
47	Temperature dependence of Al/Ti-based Ohmic contact to GaN devices: HEMT and MOSFET. Microelectronic Engineering, 2011, 88, 3140-3144.	2.4	24
48	Effect of carbon doping on crystal quality, electrical isolation and electron trapping in GaN based structures grown silicon substrates. Solid-State Electronics, 2012, 75, 86-92.	1.4	24
49	First Power Performance Demonstration of Flexible AlGaN/GaN High Electron Mobility Transistor. IEEE Electron Device Letters, 2016, 37, 553-555.	3.9	24
50	AlGaN/GaN/AlGaN DH-HEMTs grown by MBE on Si(111). Journal of Crystal Growth, 2005, 278, 393-396.	1.5	23
51	Strain engineering in GaN layers grown on silicon by molecular beam epitaxy: The critical role of growth temperature. Journal of Crystal Growth, 2009, 311, 2002-2005.	1.5	23
52	Dyakonov-Perel electron spin relaxation in a wurtzite semiconductor: From the nondegenerate to the highly degenerate regime. Physical Review B, 2011, 84, .	3.2	23
53	Optimization of ${m Al}_{0.29}{m Ga}_{0.71}{m N}/{m GaN}$ High Electron Mobility Heterostructures for High-Power/Frequency Performances. IEEE Transactions on Electron Devices, 2013, 60, 3105-3111.	3.0	22
54	Influence of AlN Growth Temperature on the Electrical Properties of Buffer Layers for GaN HEMTs on Silicon. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700637.	1.8	22

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55	Hexagonal c-axis GaN layers grown by metalorganic vapor-phase epitaxy on Si(001). Journal of Crystal Growth, 2005, 280, 44-53.	1.5	21
56	Developments for the production of high-quality and high-uniformity AlGaN/GaN heterostructures by ammonia MBE. Journal of Crystal Growth, 2007, 301-302, 434-436.	1.5	21
57	High temperature behaviour of GaN HEMT devices on Si(111) and sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1971-1973.	0.8	21
58	Blue (Ga,In)N/GaN Light Emitting Diodes on Si(110) Substrate. Applied Physics Express, 0, 1, 121101.	2.4	21
59	Surface morphology and strain relaxation of InAlAs buffer layers grown lattice mismatched on GaAs with inverse steps. Applied Surface Science, 2000, 166, 442-445.	6.1	20
60	Deposited Thin SiO[sub 2] for Gate Oxide on n-Type and p-Type GaN. Journal of the Electrochemical Society, 2010, 157, H1008.	2.9	20
61	Electrical activity at the AlN/Si Interface: identifying the main origin of propagation losses in GaN-on-Si devices at microwave frequencies. Scientific Reports, 2020, 10, 14166.	3.3	20
62	Fabrication, Characterization, and Physical Analysis of AlGaN/GaN HEMTs on Flexible Substrates. IEEE Transactions on Electron Devices, 2013, 60, 1054-1059.	3.0	19
63	AlGaNâˆ•GaN HEMTs on resistive Si(111) substrate grown by gas-source MBE. Electronics Letters, 2002, 38, 91.	1.0	18
64	Influence of MBE growth conditions on the quality of InAlAs/InGaAs metamorphic HEMTs on GaAs. Journal of Crystal Growth, 2003, 251, 822-826.	1.5	18
65	Structural and electrical properties of AlGaN/GaN HEMTs grown by MBE on SiC, Si(111) and GaN templates. Journal of Crystal Growth, 2005, 278, 383-386.	1.5	18
66	In situ measurements of wafer bending curvature during growth of group-III-nitride layers on silicon by molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 71-74.	1.5	18
67	Temperature impact and analytical modeling of the AlGaN/GaN-on-Si saturation drain current and transconductance. Semiconductor Science and Technology, 2012, 27, 125010.	2.0	18
68	Gate current analysis of AlGaN/GaN on silicon heterojunction transistors at the nanoscale. Applied Physics Letters, 2012, 101, 093505.	3.3	18
69	Molecular beam epitaxy of ferromagnetic epitaxial GdN thin films. Journal of Crystal Growth, 2014, 404, 146-151.	1.5	18
70	Highly resistive epitaxial Mg-doped GdN thin films. Applied Physics Letters, 2015, 106, .	3.3	18
71	Recent improvements of flexible GaN-based HEMT technology. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600484.	1.8	18
72	RF Performance of AlGaN/GaN High-Electron-Mobility Transistors Grown on Silicon (110). Applied Physics Express, 2011, 4, 064105.	2.4	17

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73	Graphene growth on AlN templates on silicon using propane-hydrogen chemical vapor deposition. Applied Physics Letters, 2014, 104, .	3.3	17
74	Quality and uniformity assessment of AlGaN/GaN quantum wells and HEMT heterostructures grown by molecular beam epitaxy with ammonia source. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2325-2328.	0.8	16
75	Investigation of AlGaNâˆ•AlNâˆ•GaN heterostructures for magnetic sensor application from liquid helium temperature to 300Â°C. Applied Physics Letters, 2008, 92, .	3.3	16
76	Comparison of In[sub 0.33]Al[sub 0.67]As/In[sub 0.34]Ga[sub 0.66]As on GaAs metamorphic high electron mobility transistors grown by molecular beam epitaxy with normal and inverse step on linear graded buffer layers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2513.	1.6	15
77	fmax of 490â€…GHz metamorphic In0.52Al0.48Asâˆ•In0.53Ga0.47As HEMTs on GaAs substrate. Electronics Letters, 2002, 38, 389.	1.0	15
78	60-GHz high power performance In/sub 0.35/Al/sub 0.65/As-In/sub 0-35/Ga/sub 0.65/As metamorphic HEMTs on GaAs. IEEE Electron Device Letters, 2003, 24, 724-726.	3.9	15
79	AlGaN/GaN HEMTs grown on silicon (001) substrates by molecular beam epitaxy. Superlattices and Microstructures, 2006, 40, 295-299.	3.1	15
80	Gate traps inducing band-bending fluctuations on AlGaN/GaN heterojunction transistors. Applied Physics Letters, 2013, 102, 023511.	3.3	15
81	High temperature electrical investigations of (Al,Ga)N/GaN heterostructures - Hall sensor applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1438-1443.	0.8	14
82	Young's modulus extraction of epitaxial heterostructure AlGaN/GaN for MEMS application. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1655-1659.	1.8	14
83	Nanoscale conductive pattern of the homoepitaxial AlGaN/GaN transistor. Nanotechnology, 2015, 26, 115203.	2.6	14
84	Electron mobility and transfer characteristics in AlGaN/GaN HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2720-2723.	0.8	13
85	Growth of wurtzite-GaN on silicon (100) substrate by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2187-2190.	0.8	13
86	AlGaN/GaN HEMTs on a (001)-Oriented Silicon Substrate Based on 100-nm SiN Recessed Gate Technology for Microwave Power Amplification. IEEE Transactions on Electron Devices, 2007, 54, 2843-2848.	3.0	13
87	Subsurface Fe-doped semi-insulating GaN templates for inhibition of regrowth interface pollution in AlGaN/GaN HEMT structures. Journal of Crystal Growth, 2008, 310, 948-954.	1.5	13
88	AlGaN/GaN high electron mobility transistor grown by molecular beam epitaxy on Si(110): comparisons with Si(111) and Si(001). Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1020.	0.8	13
89	Voltage-controlled sub-terahertz radiation transmission through GaN quantum well structure. Applied Physics Letters, 2011, 99, 082101.	3.3	13
90	Nanoscale investigation of AlGaN/GaN-on-Si high electron mobility transistors. Nanotechnology, 2012, 23, 395204.	2.6	13

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91	Integration of Micro Resistance Thermometer Detectors in AlGaN/GaN Devices. IEEE Journal of the Electron Devices Society, 2014, 2, 145-148.	2.1	13
92	Magnetic properties of Gdâ€doped GaN. Physica Status Solidi (B): Basic Research, 2014, 251, 1673-1684.	1.5	13
93	Influence of 3Câ€“SiC/Si (111) template properties on the strain relaxation in thick GaN films. Journal of Crystal Growth, 2014, 398, 23-32.	1.5	13
94	Al(Ga)N/GaN high electron mobility transistors on silicon. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1049-1058.	1.8	13
95	Room-Temperature AlGaN/GaN Terahertz Plasmonic Detectors with a Zero-Bias Grating. Journal of Infrared, Millimeter, and Terahertz Waves, 2016, 37, 243-257.	2.2	13
96	Trap states analysis in AlGaN/AlN/GaN and InAlN/AlN/GaN high electron mobility transistors. Current Applied Physics, 2017, 17, 1601-1608.	2.4	13
97	Enhancement mode metamorphic Al/sub 0.67/In/sub 0.33/As/Ga/sub 0.66/In/sub 0.34/As HEMT on GaAs substrate with high breakdown voltage. IEEE Electron Device Letters, 2000, 21, 512-514.	3.9	12
98	Stress distribution of 12 Î¼m thick crack free continuous GaN on patterned Si(110) substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 425-428.	0.8	12
99	Characterization of m-GaN and a-GaN Crystallographic Planes after Being Chemically Etched in TMAH Solution. Energies, 2021, 14, 4241.	3.1	12
100	High-power AlGaNâˆ•GaN HEMTs on resistive silicon substrate. Electronics Letters, 2002, 38, 750.	1.0	11
101	AlGaN/GaN HEMTs with an InGaN backâ€barrier grown by ammoniaâ€assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 480-483.	1.8	11
102	Structural and electrical properties of AlN thin films on GaN substrates grown by plasma enhanced-Atomic Layer Deposition. Materials Science in Semiconductor Processing, 2019, 97, 35-39.	4.0	11
103	Temperature dependence of GaAs chemical etching using AsCl3. Journal of Crystal Growth, 1996, 164, 97-103.	1.5	10
104	Thermal characterisation of AlGaN/GaN HEMTs grown on silicon and sapphire substrates based on pulsed I-V measurements. EPJ Applied Physics, 2003, 22, 77-82.	0.7	10
105	Electronic properties of deep defects in n-type GaN. Superlattices and Microstructures, 2004, 36, 435-443.	3.1	10
106	Temperature measurement in AlGaN/GaN High-Electron-Mobility Transistors using micro-Raman scattering spectroscopy. EPJ Applied Physics, 2005, 30, 77-82.	0.7	10
107	AlGaNâˆ•GaN HEMTs on (001) silicon substrates. Electronics Letters, 2006, 42, 117.	1.0	10
108	Magnetotransport in Gd-implanted wurtzite GaNâˆ•AlxGa1â^'xN high electron mobility transistor structures. Applied Physics Letters, 2008, 92, 112111.	3.3	10

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109	Bulk Temperature Impact on the AlGaN/GaN HEMT Forward Current on Si, Sapphire and Free-Standing GaN. ECS Solid State Letters, 2012, 2, P4-P7.	1.4	10
110	Growth optimization and characterization of lattice-matched Al0.82In0.18N optical confinement layer for edge emitting nitride laser diodes. Journal of Crystal Growth, 2012, 338, 20-29.	1.5	10
111	High temperature annealing and CVD growth of few-layer graphene on bulk AlN and AlN templates. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600436.	1.8	10
112	2 W mm^{â˜'1} power density of an AlGaN/GaN HEMT grown on free-standing GaN substrate at 40 GHz. Semiconductor Science and Technology, 2019, 34, 12LT01.	2.0	10
113	0.1-Î¼m high performance double heterojunction In0.32Al0.68As/In0.33Ga0.67As metamorphic HEMTs on GaAs. Solid-State Electronics, 2000, 44, 1685-1688.	1.4	9
114	Realization of AlGaN/GaN HEMTs on 3Câ€šSiC/Si(111) substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1983-1985.	0.8	9
115	High temperature behaviour of AlGaN/AlN/GaN Hall-FET sensors. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 1-4.	3.5	9
116	Signature of monolayer and bilayer fluctuations in the width of (Al,Ga)N/GaN quantum wells. Physical Review B, 2009, 79, .	3.2	9
117	Delta-Doping of Epitaxial GaN Layers on Large Diameter Si(111) Substrates. Applied Physics Express, 2012, 5, 025504.	2.4	9
118	Assessment of transistors based on GaN on silicon substrate in view of integration with silicon technology. Semiconductor Science and Technology, 2013, 28, 094003.	2.0	9
119	On the correlation between kink effect and effective mobility in InAlN/GaN HEMTs. , 2014, , .		9
120	AlGaN/GaN HEMTs with very thin buffer on Si (111) for nanosystems applications. Semiconductor Science and Technology, 2014, 29, 115018.	2.0	9
121	Growth of nitrideâ€based light emitting diodes with a highâ€reflectivity distributed Bragg reflector on mesaâ€patterned silicon substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2297-2301.	1.8	9
122	Anomalous DC and RF behavior of virgin AlGaN/AlN/GaN HEMTs. Semiconductor Science and Technology, 2017, 32, 035011.	2.0	9
123	Trapping Dipolar Exciton Fluids in GaN/(AlGa)N Nanostructures. Nano Letters, 2019, 19, 4911-4918.	9.1	9
124	Modelling of pseudomorphic AlGaAs/GaInAs/AlGaAs layers using selfconsistent approach. European Transactions on Telecommunications, 1990, 1, 429-432.	1.2	8
125	0.1 [micro sign]m high performance metamorphic In0.32Al0.68As/In0.33Ga0.67As HEMT on GaAs using inverse step InAlAs buffer. Electronics Letters, 1999, 35, 1670.	1.0	8
126	Stacking of metamorphic InAlAs/InGaAs heterostructures on GaAs substrate. Journal of Applied Physics, 2001, 90, 5774-5777.	2.5	8

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127	Role of Substrate Misorientation in Relaxation of 3C-SiC Layers on Silicon. Materials Science Forum, 0, 615-617, 169-172.	0.3	8
128	A comparative study of graphene growth on SiC by hydrogen-CVD or Si sublimation through thermodynamic simulations. CrystEngComm, 2018, 20, 3702-3710.	2.6	8
129	Metalorganic Chemical Vapor Phase Epitaxy Growth of Buffer Layers on 3Câ€šiC/Si(111) Templates for AlGaN/GaN High Electron Mobility Transistors with Low RF Losses. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900760.	1.8	8
130	High pressure study of the electrical transport phenomena in AlGaN/GaN heterostructures. Physica Status Solidi (B): Basic Research, 2003, 235, 232-237.	1.5	7
131	Power results at 4 GHz of AlGaN/GaN HEMTs on high resistive silicon [111] substrate. IEEE Microwave and Wireless Components Letters, 2003, 13, 99-101.	3.2	7
132	Temperature measurement by micro-Raman scattering spectroscopy in the active zone of AlGaN/GaN high-electron-mobility transistors. EPJ Applied Physics, 2004, 27, 293-296.	0.7	7
133	Advances in quality and uniformity of (Al,Ga)N/GaN quantum wells grown by molecular beam epitaxy with plasma source. Journal of Crystal Growth, 2009, 311, 2029-2032.	1.5	7
134	Bias Dependence of Gallium Nitride Micro-Electro-Mechanical Systems Actuation Using a Two-Dimensional Electron Gas. Applied Physics Express, 2012, 5, 067201.	2.4	7
135	AlGaN/GaN high electron mobility transistors on diamond substrate obtained through aluminum nitride bonding technology. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, .	1.2	7
136	Composition analysis of semiconductor quantum wells by energy filtered convergent-beam electron diffraction. Ultramicroscopy, 2008, 108, 358-366.	1.9	6
137	Evaluation of SiN films for AlGaN/GaN MISâ€HEMTs on Si(111). Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1016.	0.8	6
138	Selective area growth of GaN-based structures by molecular beam epitaxy on micrometer and nanometer size patterns. Materials Science in Semiconductor Processing, 2009, 12, 16-20.	4.0	6
139	Effects of substrate orientation on the optical anisotropy spectra of GaN/AlN/Si heterostructures in the energy range from 2.0 to 3.5â€‰eV. Journal of Applied Physics, 2012, 111, .	2.5	6
140	Fabrication and growth of GaN-based micro and nanostructures. International Journal of Nanotechnology, 2012, 9, 412.	0.2	6
141	Impact of the Bending on the Electroluminescence of Flexible InGaN/GaN Light-Emitting Diodes. IEEE Photonics Technology Letters, 2016, 28, 1661-1664.	2.5	6
142	GaN films and GaN/AlGaN quantum wells grown by plasma assisted molecular beam epitaxy using a high density radical source. Journal of Crystal Growth, 2016, 433, 165-171.	1.5	6
143	AlGaN/GaN/AlGaN DHâ€HEMTs Grown on a Patterned Silicon Substrate. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700642.	1.8	6
144	Kapitza thermal resistance characterization of epitaxial grapheneâ€“SiC(0001) interface. Applied Physics Letters, 2019, 114, .	3.3	6

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145	Terahertz intersubband absorption of GaN/AlGaN step quantum wells grown by MOVPE on Si(111) and Si(110) substrates. Applied Physics Letters, 2019, 115, .	3.3	6
146	Stability of the threshold voltage in fluorine-implanted normally-off AlN/GaN HEMTs co-integrated with commercial normally-on GaN HEMT technology. Microelectronics Reliability, 2021, 126, 114291.	1.7	6
147	Nanoscale structural and electrical properties of graphene grown on AlGaN by catalyst-free chemical vapor deposition. Nanotechnology, 2021, 32, 015705.	2.6	6
148	In-Situ Cleaning ofSiO2-Patterned GaAs Surface with Trisdimethylaminoarsine for Selective Regrowth. Japanese Journal of Applied Physics, 1996, 35, 5964-5968.	1.5	5
149	Hemtâ€™s capability for millimeter wave applications. Annales Des Telecommunications/Annals of Telecommunications, 2001, 56, 15-26.	2.5	5
150	Influence of crystal quality on electron mobility in AlGaN/GaN HEMTs grown on Si(111), SiC and GaN templates. European Physical Journal Special Topics, 2006, 132, 365-368.	0.2	5
151	Strain in 3Câ€“SiC Heteroepitaxial Layers Grown on (100) and (111) Oriented Silicon Substrates. Materials Science Forum, 2008, 600-603, 207-210.	0.3	5
152	Windowed growth of AlGaN/GaN heterostructures on Silicon ã€˜111ã€‰ substrates for future MOS integration. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 371-374.	1.8	5
153	GaN: A multifunctional material enabling MEMS resonators based on amplified piezoelectric detection. , 2011, , .		5
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